



30V Complementary Enhancement Mode MOSFET

Voltage

30/-30 V

Current

18.5/-18A

Features

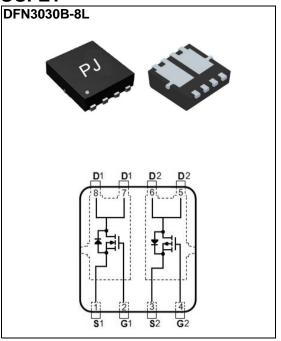
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3030B-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0008 ounces, 0.022 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	N-CH LIMIT	P-CH LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		V	
Continuous Drain Current (Note 4)	T _C =25°C		18.5	-18	A	
	T _C =100°C	I _D	11.5	-11		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	74	-72		
B Bississitis	T _C =25°C	ı	17.8		W	
Power Dissipation	T _C =100°C	Pb	7			
Continuous Drain Current (Note 4)	T _A =25°C	I _D	6.4	6.4	A	
	T _A =70°C		5.1	5.1		
B Bississitis	T _A =25°C	ı	1.3		W	
Power Dissipation	T _A =70°C	PD				
Operating Junction and Storage Temperature Range		T_J , T_{STG}	-55~150		°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	7	7	°0000	
	Junction to Ambient	$R_{\theta JA}$	62.5		°C/W	





N-CH Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.3	2.1	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =6A	-	23	28	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =4.5V, I_D =3A	-	36	43	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V _{DS} =15V, I _D =6A, V _{GS} =10V ^(Note 2,3)	-	7.8	-	nC
Gate-Source Charge	Q _{gs}		-	1.2	-	
Gate-Drain Charge	Q_{gd}		-	1.5	-	
Input Capacitance	Ciss	V_{DS} =15V, V_{GS} =0V, f =1MHZ	-	343	-	pF
Output Capacitance	Coss		-	48	-	
Reverse Transfer Capacitance	Crss		-	34	-	
Turn-On Delay Time	td _(on)	V_{DD} =15V, I_{D} =6A, V_{GS} =10V, R_{G} =3 Ω (Note 2,3)	-	3	-	
Turn-On Rise Time	t _r		-	40	-	
Turn-Off Delay Time	td _(off)		-	38	-	ns
Turn-Off Fall Time	t _f		-	39	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					10.5	
Diode Forward Current	I _S		-	-	18.5	Α
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.78	1.2	V





P-CH Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1	-1.6	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4A	-	26	31	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V,I _D =-2A	-	36	45	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V _{DS} =-15V, I _D =-5A, V _{GS} =-4.5V (Note 2,3)	-	7.8	-	nC
Gate-Source Charge	Q_gs		-	2.7	-	
Gate-Drain Charge	Q_{gd}		-	2.8	-	
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V,	-	870	-	pF
Output Capacitance	Coss		-	130	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	93	-	
Turn-On Delay Time	td _(on)	V_{DS} =-15V,ID=-1A, V_{GS} =-10V, R_G =6 Ω (Note 2,3)	-	6.5	-	
Turn-On Rise Time	t _r		-	8.8	-	
Turn-Off Delay Time	td _(off)		-	73	-	ns
Turn-Off Fall Time	t _f		-	44	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	_			-	-18	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.75	-1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper..
- 6. Guaranteed by design, not subject to production testing.





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PJQ4602

N-CH TYPICAL CHARACTERISTIC CURVES

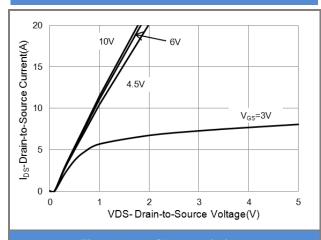
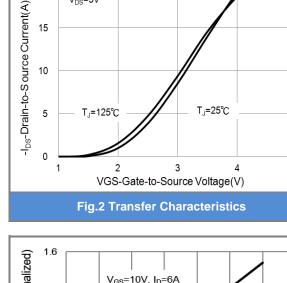


Fig.1 Output Characteristics



20

15

 V_{DS} =5V

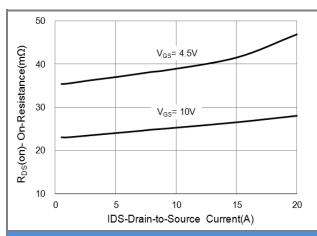


Fig.3 On-Resistance vs. Drain Current

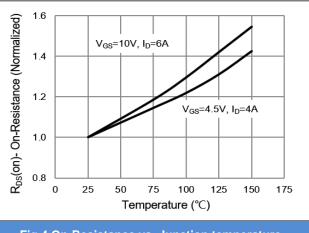
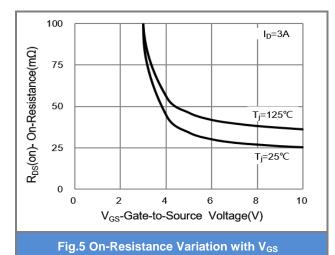


Fig.4 On-Resistance vs. Junction temperature



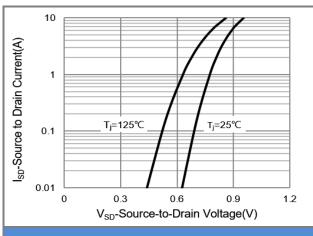


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

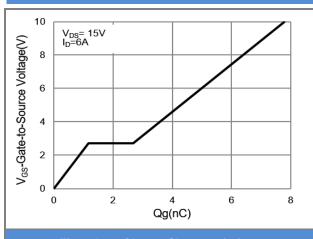


Fig.7 Gate-Charge Characteristics

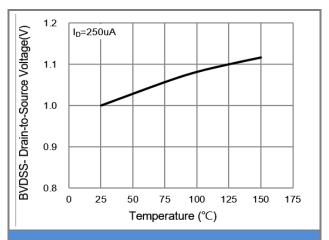


Fig.8 Breakdown Voltage Variation vs. Temperature

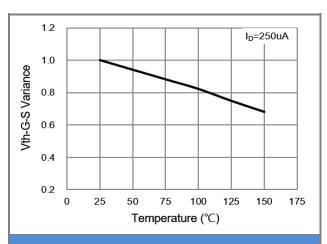


Fig.9 Threshold Voltage Variation with Temperature

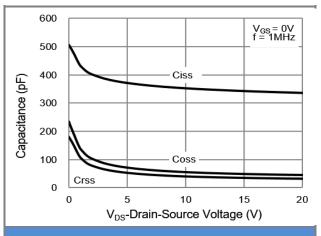


Fig.10 Capacitance vs. Drain-Source Voltage

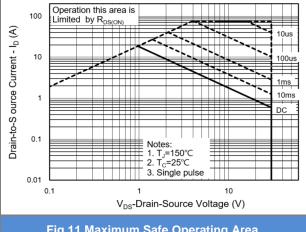


Fig.11 Maximum Safe Operating Area

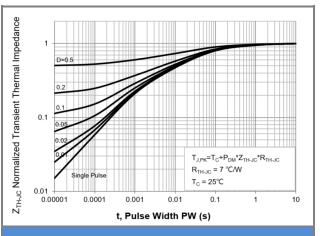


Fig.12 Normalized Transient Thermal Impedance





P-CH TYPICAL CHARACTERISTIC CURVES

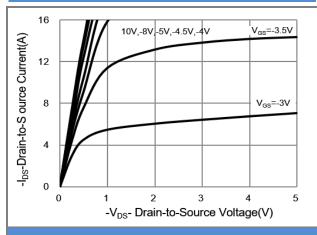


Fig.13 Output Characteristics

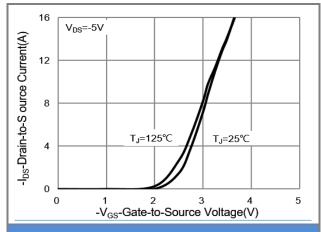


Fig.14 Transfer Characteristics

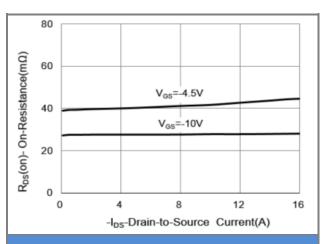


Fig.15 On-Resistance vs. Drain Current

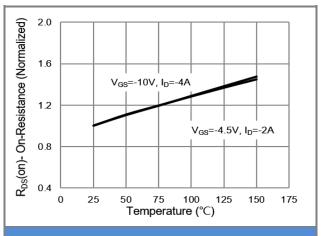


Fig.16 On-Resistance vs. Junction temperature

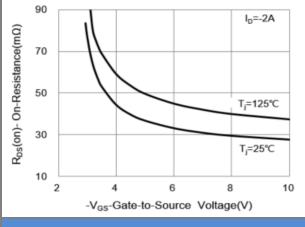


Fig.17 On-Resistance Variation with V_{GS}

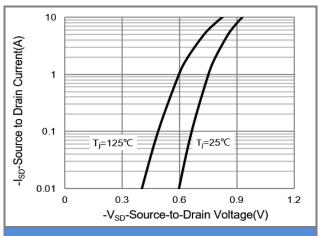


Fig.18 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

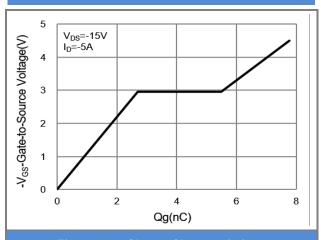


Fig.19 Gate-Charge Characteristics

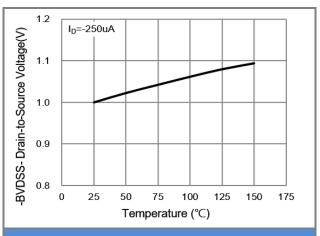


Fig.20 Breakdown Voltage Variation vs. Temperature

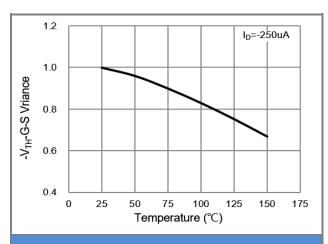


Fig.21 Threshold Voltage Variation with Temperature

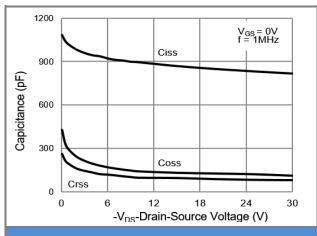


Fig.22 Capacitance vs. Drain-Source Voltage

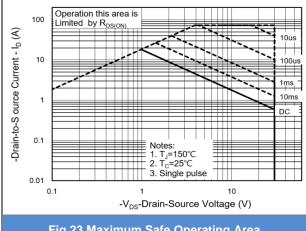


Fig.23 Maximum Safe Operating Area

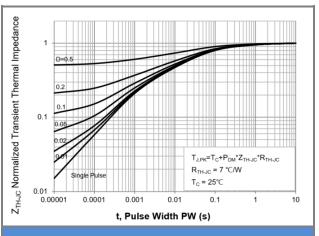


Fig.24 Normalized Transient Thermal Impedance

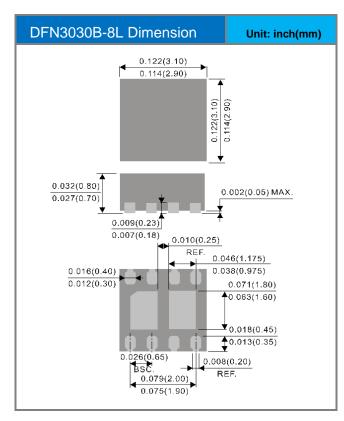


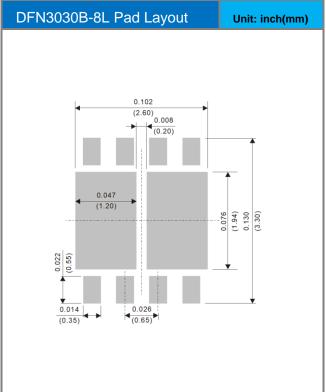


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4602_R1_00001	DFN3030B-8L	3K pcs / 7" reel	4602	Halogen free

Packaging Information & Mounting Pad Layout









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